

NCE P-Channel Enhancement Mode Power MOSFET

Description

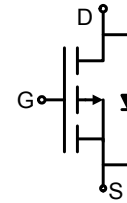
The NCE30P06J uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages. This device is suitable for use as a load switching application and a wide variety of other applications.

General Features

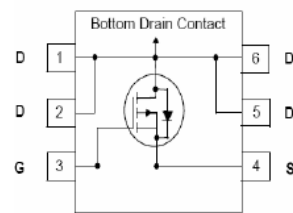
- $V_{DS} = -30V, I_D = -6.5A$
 $R_{DS(ON)} < 30m\Omega @ V_{GS} = -10V$
 $R_{DS(ON)} < 50m\Omega @ V_{GS} = -4.5V$
- Advanced trench MOSFET process technology
- Ultra low on-resistance with low gate charge

Application

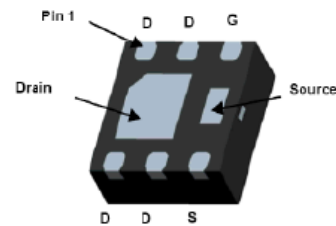
- PWM applications
- Load switch
- Battery charge in cellular handset



Schematic diagram



Pin assignment



DFN2X2-6L bottom view

Package marking and ordering information

Device Marking	Device	Device Package	Reel Size	Tape Width	Quantity
NCE30P06J	NCE30P06J	DFN2X2-6L	-	-	-

Absolute maximum ratings ($T_C = 25^\circ C$ unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	-30	V
Gate-Source Voltage	V_{GS}	± 20	V
Drain Current-Continuous	I_D	-6.5	A
Drain Current -Pulsed (Note 1)	I_{DM}	-30	A
Maximum Power Dissipation	P_D	2.8	W
Operating Junction and Storage Temperature Range	T_J, T_{STG}	-55 To 150	$^\circ C$

Thermal Characteristic

Parameter	Symbol	Typ.	Max	Unit
Thermal Resistance, Junction-to-Case (Note 2)	$R_{\theta JA}$	66	80	$^\circ C/W$

Electrical characteristics (T_A=25°C unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V I _D =-250μA	-30	-33	-	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =-30V, V _{GS} =0V	-	-	-1	μA
Gate-Body Leakage Current	I _{GSS}	V _{GS} =±20V, V _{DS} =0V	-	-	±100	nA
On Characteristics (Note 3)						
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} , I _D =-250μA	-1.0	-1.3	-2.0	V
Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} =-10V, I _D =-6.5A	-	24	30	mΩ
		V _{GS} =-4.5V, I _D =-5A	-	34	50	
Forward Transconductance	g _{FS}	V _{DS} =-5V, I _D =-6.5A		10	-	S
Dynamic Characteristics (Note 4)						
Input Capacitance	C _{ISS}	V _{DS} =-15V, V _{GS} =0V, F=1.0MHz	-	520	-	PF
Output Capacitance	C _{OSS}		-	100	-	PF
Reverse Transfer Capacitance	C _{RSS}		-	65	-	PF
Switching Characteristics (Note 4)						
Turn-on Delay Time	t _{d(on)}	V _{DD} =-15V, R _L =2.3Ω V _{GS} =-10V, R _{GEN} =6Ω	-	7.5	-	nS
Turn-on Rise Time	t _r		-	5.5	-	nS
Turn-Off Delay Time	t _{d(off)}		-	19	-	nS
Turn-Off Fall Time	t _f		-	7	-	nS
Total Gate Charge	Q _g	V _{DS} =-15V, I _D =-6.5A V _{GS} =-10V	-	9.2	-	nC
Gate-Source Charge	Q _{gs}		-	1.6	-	nC
Gate-Drain Charge	Q _{gd}		-	2.2	-	nC
Drain-Source Diode Characteristics						
Diode Forward Voltage (Note 3)	V _{SD}	V _{GS} =0V, I _S =-6.5A	-	-	-1.2	V

Notes:

1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board, t ≤ 10 sec.
3. Pulse Test: Pulse Width ≤ 300μs, Duty Cycle ≤ 2%.
4. Guaranteed by design, not subject to production

P- Channel Typical Electrical and Thermal Characteristics (Curves)

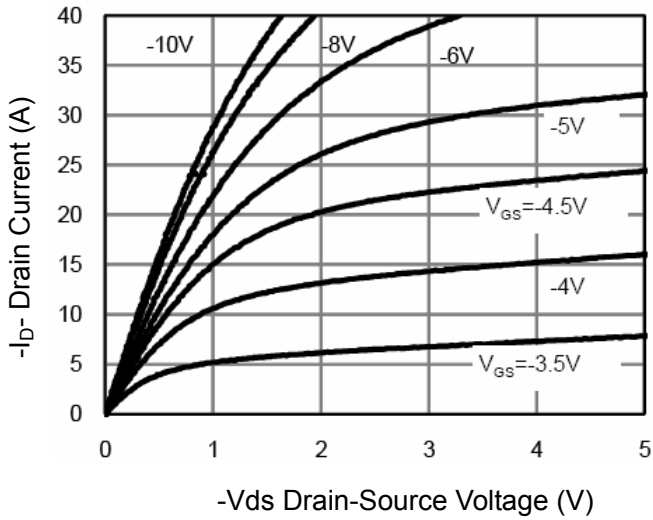


Figure 1 Output Characteristics

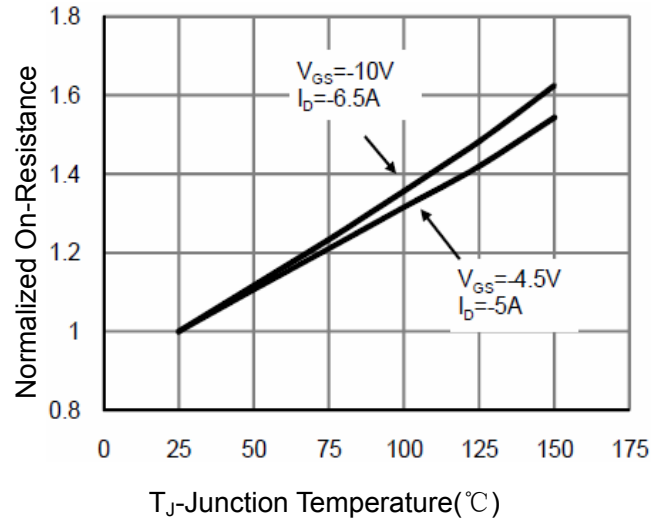


Figure 4 Rdson-Junction Temperature

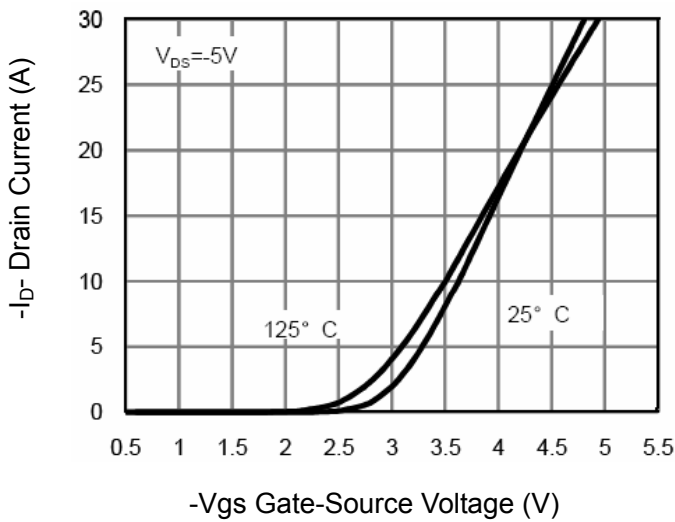


Figure 2 Transfer Characteristics

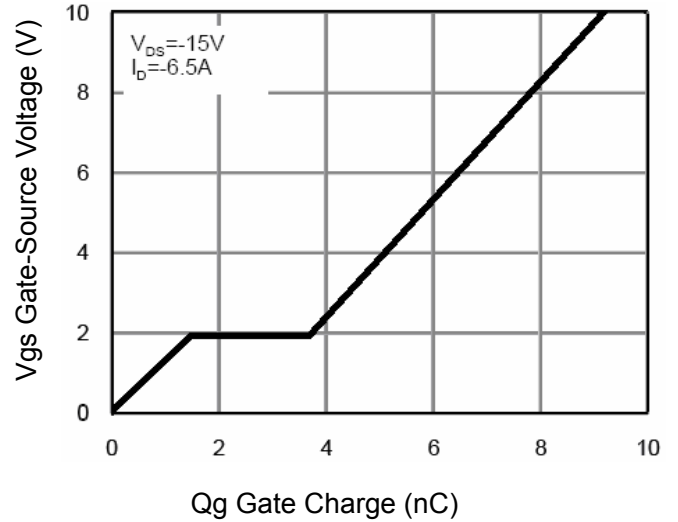


Figure 5 Gate Charge

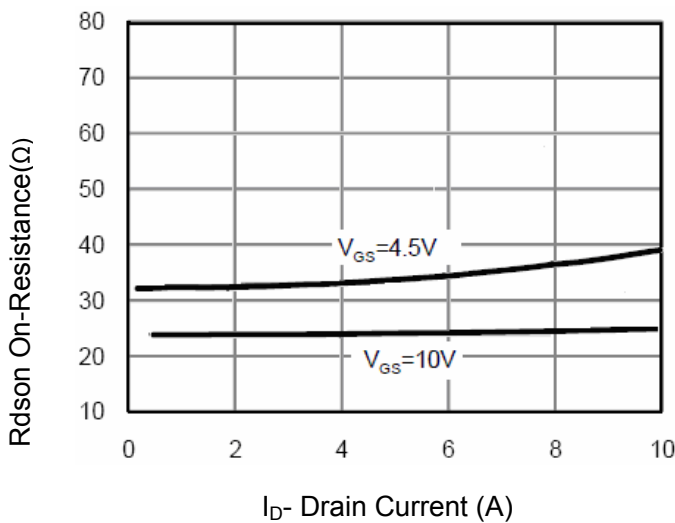


Figure 3 Rdson- Drain Current

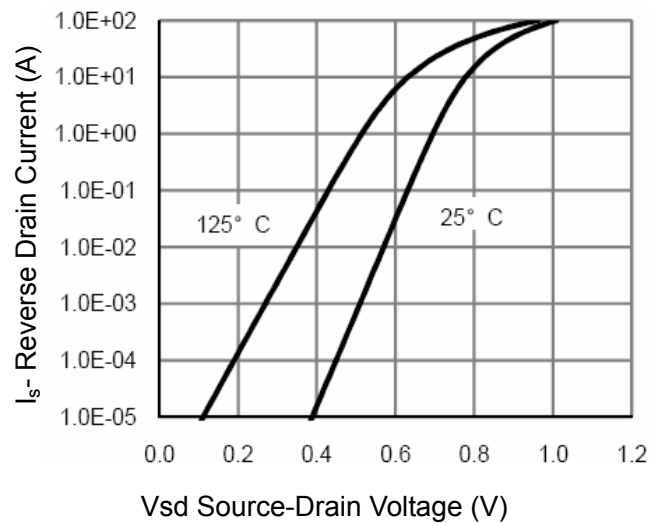


Figure 6 Source- Drain Diode Forward

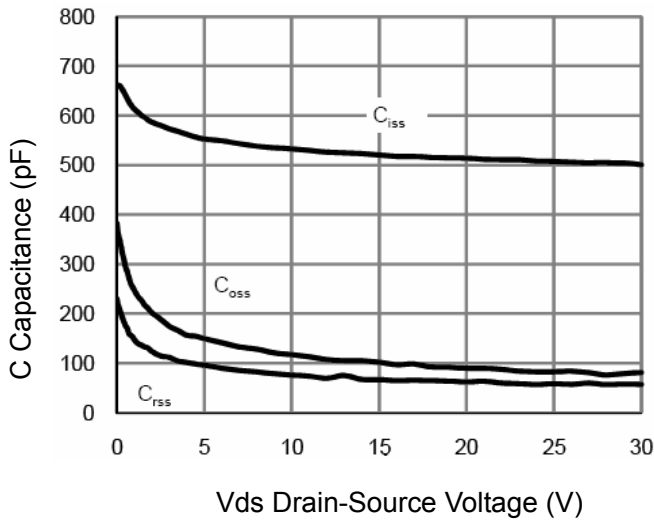


Figure 7 Capacitance vs Vds

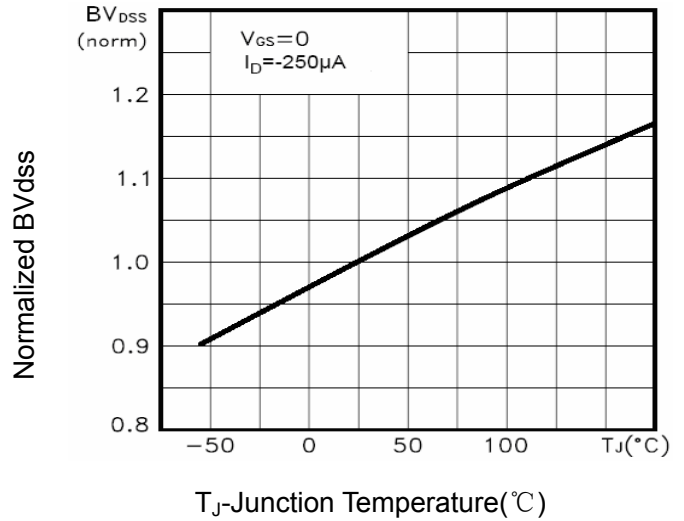


Figure 9 BV_{DSS} vs Junction Temperature

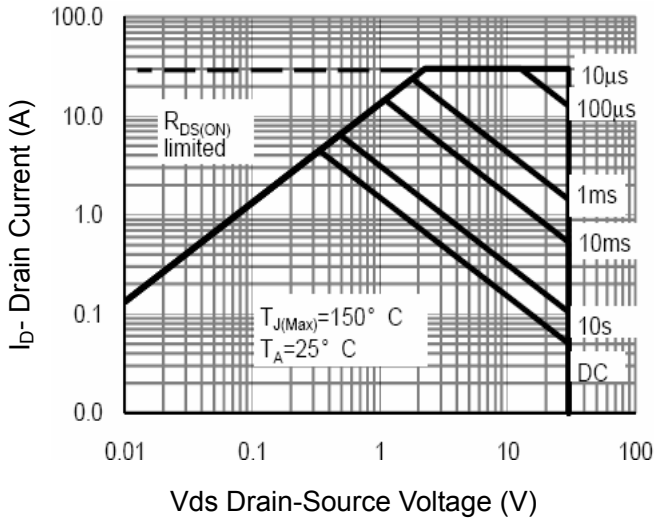


Figure 8 Safe Operation Area

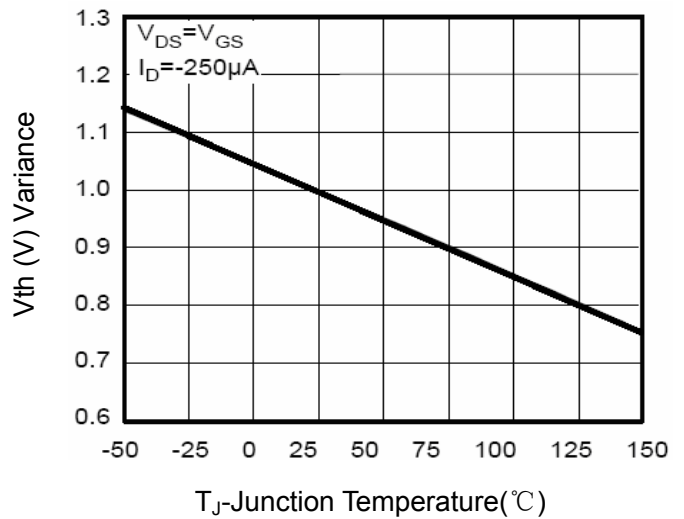


Figure 10 $V_{GS(th)}$ vs Junction Temperature

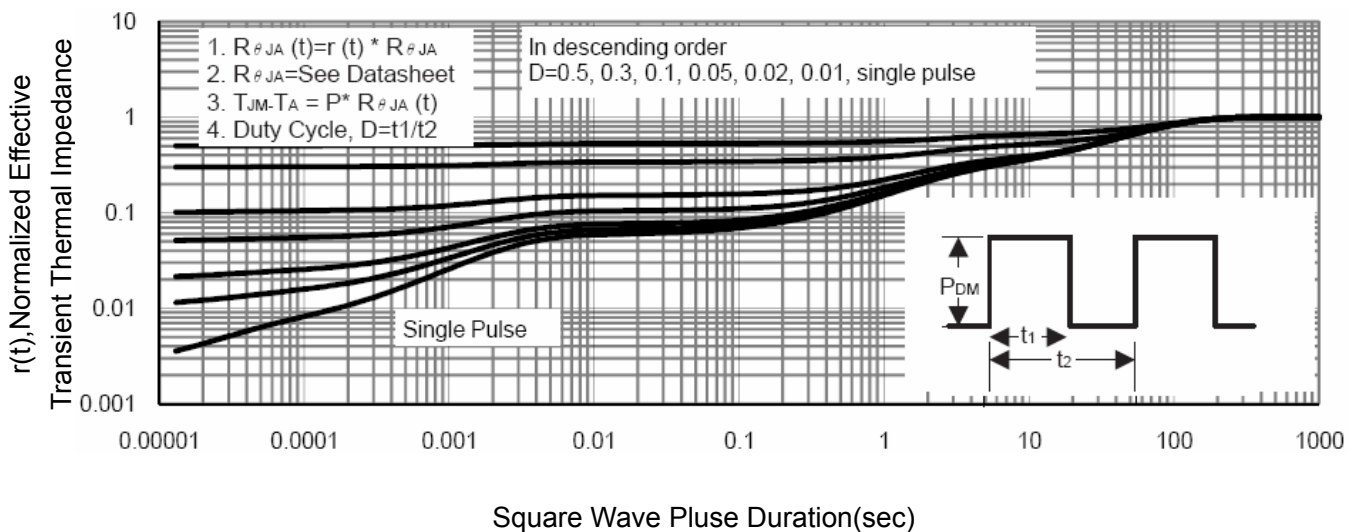
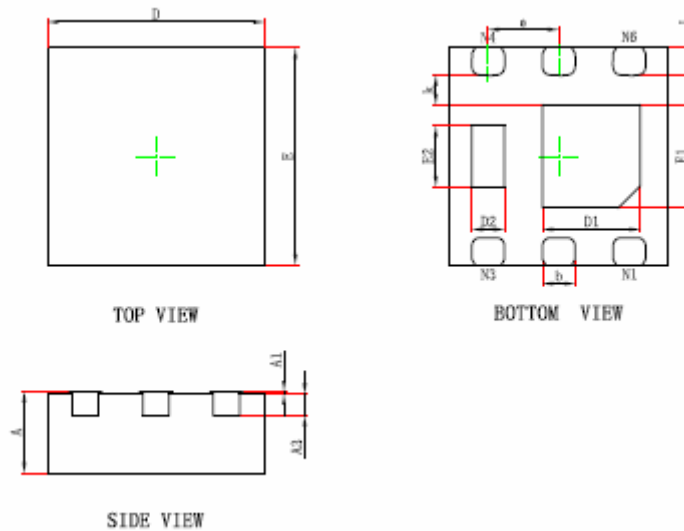


Figure 11 Normalized Maximum Transient Thermal Impedance

DFN2X2-6L Package Information


Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	0.700	0.800	0.028	0.031
A1	0.000	0.050	0.000	0.002
A3	0.203REF.		0.008REF.	
D	1.924	2.076	0.076	0.082
E	1.924	2.076	0.076	0.082
D1	0.800	1.000	0.031	0.039
E1	0.850	1.050	0.033	0.041
D2	0.200	0.400	0.008	0.016
E2	0.460	0.660	0.018	0.026
k	0.200MIN.		0.008MIN.	
b	0.250	0.350	0.010	0.014
e	0.650TYP.		0.026TYP.	
L	0.174	0.326	0.007	0.013

Notes

1. All dimensions are in millimeters.
2. Tolerance $\pm 0.10\text{mm}$ (4 mil) unless otherwise specified
3. Package body sizes exclude mold flash and gate burrs. Mold flash at the non-lead sides should be less than 5 mils.
4. Dimension L is measured in gauge plane.
5. Controlling dimension is millimeter, converted inch dimensions are not necessarily exact.

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